

NPN General Purpose Amplifier

This device is designed as a general purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

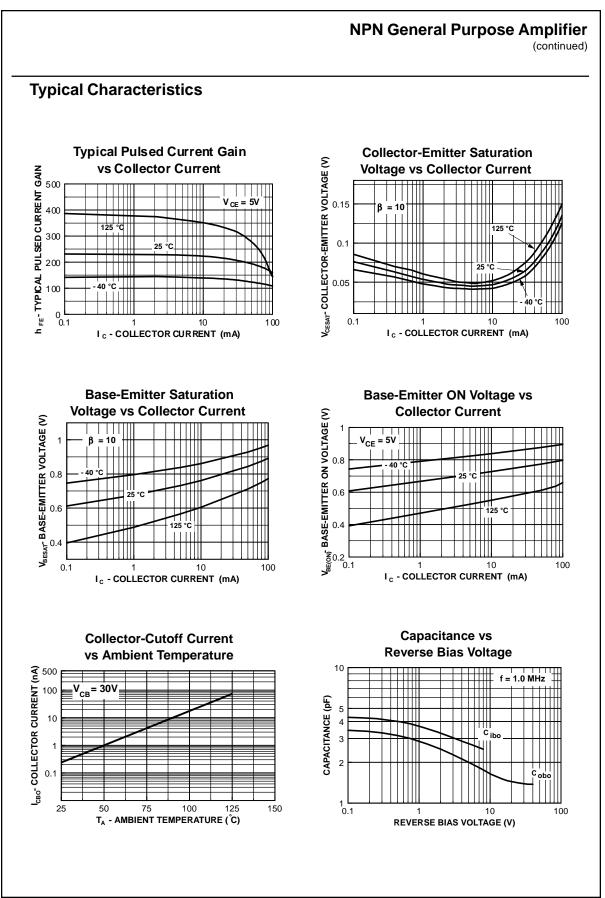
Thermal Characteristics TA = 25°C unless otherwise noted

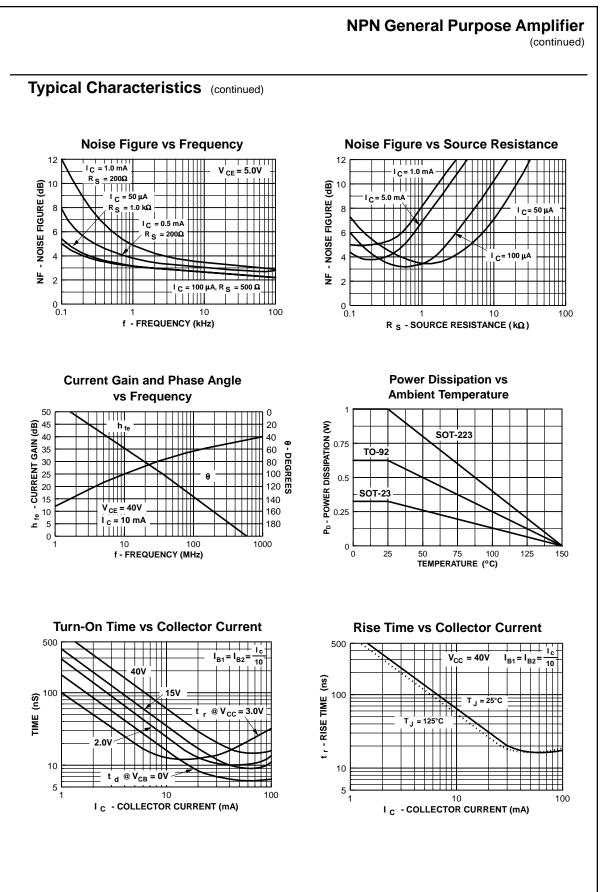
Symbol	Characteristic	Мах		Units
		2N4124	*MMBT4124	
P _D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

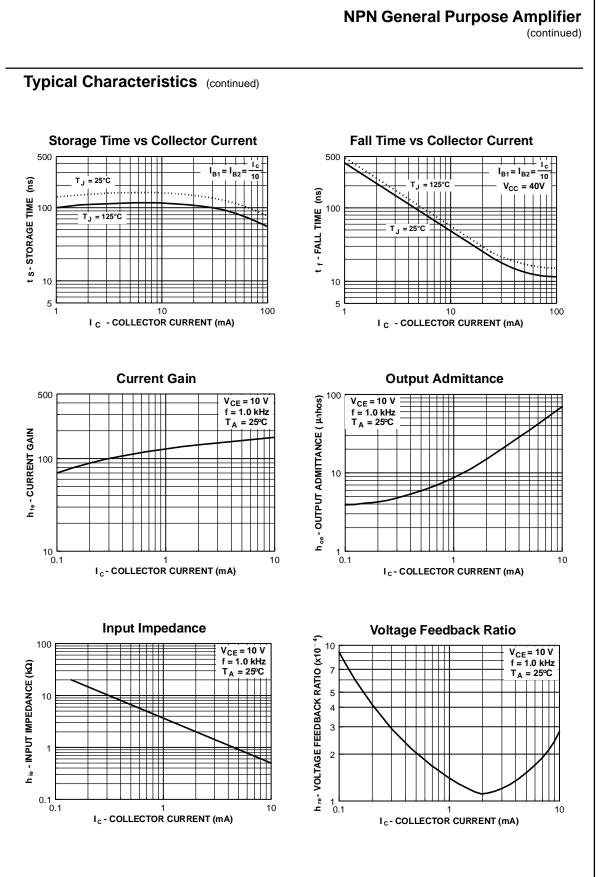
*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAP	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	25		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	30		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0$		50	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, \text{ I}_{C} = 0$		50	nA
	ACTERISTICS*				
	DC Current Gain	I _C = 2.0 mA, V _{CE} = 1.0 V	120	360	
··rE		$I_{\rm C} = 2.0$ mA, $V_{\rm CE} = 1.0$ V $I_{\rm C} = 50$ mA, $V_{\rm CE} = 1.0$ V	60	500	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		0.3	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 50$ mA, $I_{\rm B} = 5.0$ mA		0.95	V
SMALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	300		MHz
C _{obo}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ f = 100 kHz		4.0	pF
C _{ibo}	Input Capacitance	$V_{BE} = 0.5 \text{ V}, I_C = 0,$ f = 1.0 kHz		8.0	pF
C _{cb}	Collector-Base Capcitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ f = 100 kHz		4.0	pF
h _{fe} NF	Small-Signal Current Gain	$V_{CE} = 10 \text{ V}, I_C = 2.0 \text{ mA},$ f = 1.0 kHz	120	480	dD
INF	Noise Figure	I_{C} = 100 μA, V _{CE} = 5.0 V, R _S =1.0kΩ, f=10 Hz to 15.7 kHz		5.0	dB







NPN General Purpose Amplifier (continued)



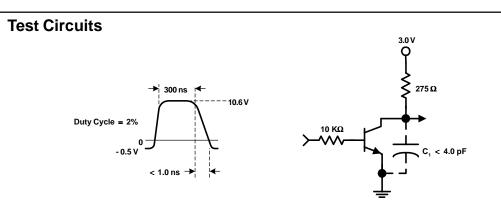
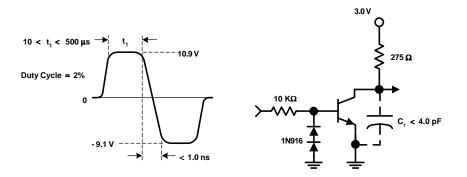


FIGURE 1: Delay and Rise Time Equivalent Test Circuit







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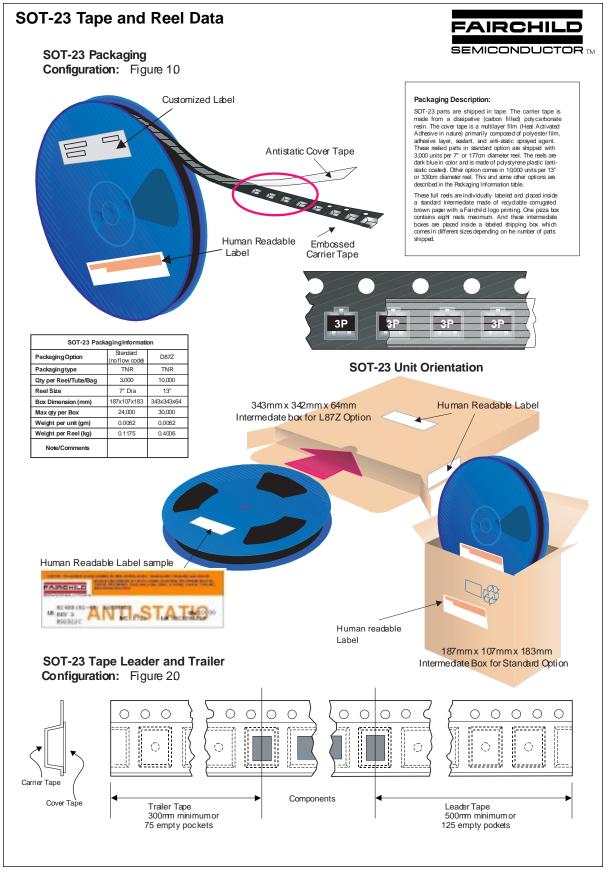
March 2001, Rev. B1





July 1999, Rev. A



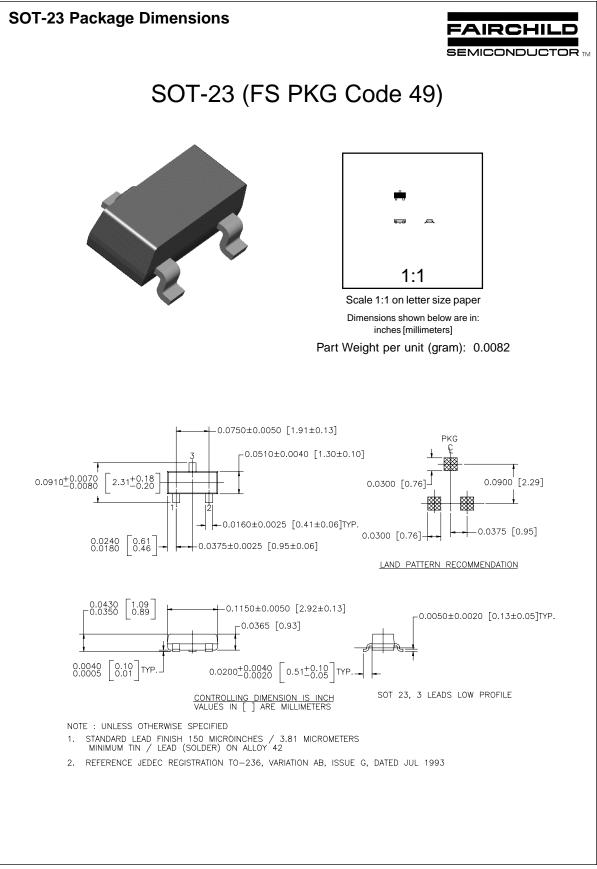


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